

MOSFETs Silicon N-channel MOS (U-MOS<sup>Ⅷ</sup>)

# TPN2R203NC

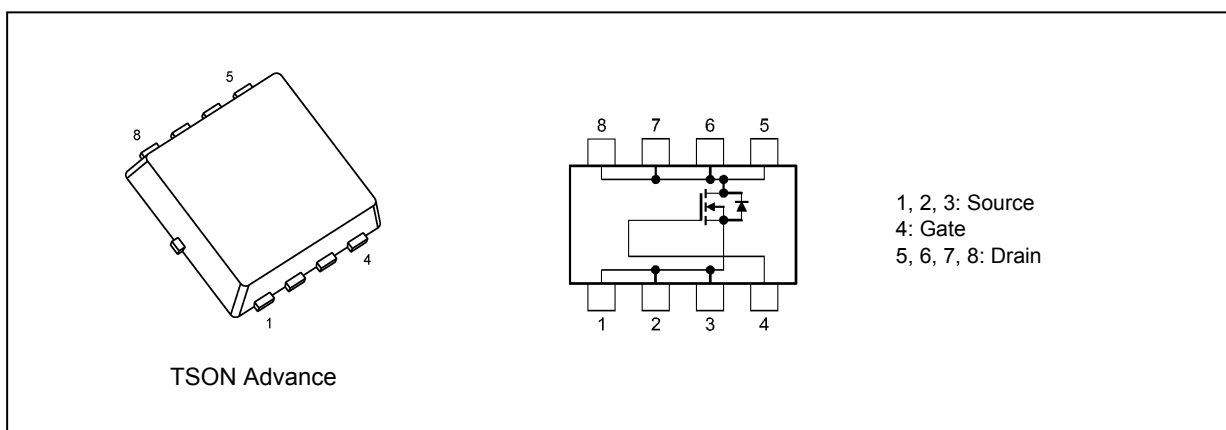
## 1. Applications

- Power Management Switches

## 2. Features

- Low drain-source on-resistance:  $R_{DS(ON)} = 1.8 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 30 \text{ V}$ )
- Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 0.5 \text{ mA}$ )

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	30	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current (DC) (Silicon limit) (Note 1), (Note 2)	$I_D$	100	A
Drain current (DC) ( $T_c = 25 \text{ }^\circ\text{C}$ ) (Note 1)	$I_D$	45	A
Drain current (pulsed) ( $t = 1 \text{ ms}$ ) (Note 1)	$I_{DP}$	200	A
Power dissipation ( $T_c = 25 \text{ }^\circ\text{C}$ )	$P_D$	42	W
Power dissipation ( $t = 10 \text{ s}$ ) (Note 3)	$P_D$	1.9	W
Power dissipation ( $t = 10 \text{ s}$ ) (Note 4)	$P_D$	0.7	W
Single-pulse avalanche energy (Note 5)	$E_{AS}$	126	mJ
Avalanche current	$I_{AR}$	45	A
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

## 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance ( $T_c = 25\text{ }^{\circ}\text{C}$ )	$R_{th(ch-c)}$	2.97	$^{\circ}\text{C/W}$
Channel-to-ambient thermal resistance ( $t = 10\text{ s}$ ) (Note 3)	$R_{th(ch-a)}$	65.7	$^{\circ}\text{C/W}$
Channel-to-ambient thermal resistance ( $t = 10\text{ s}$ ) (Note 4)	$R_{th(ch-a)}$	178	$^{\circ}\text{C/W}$

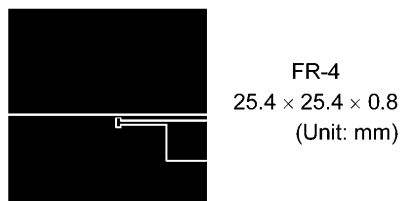
Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^{\circ}\text{C}$ .

Note 2: Limited by silicon chip capability.

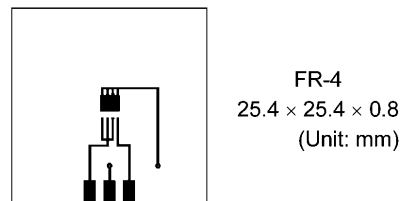
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD} = 24\text{ V}$ ,  $T_{ch} = 25\text{ }^{\circ}\text{C}$  (initial),  $L = 0.048\text{ mH}$ ,  $I_{AR} = 45\text{ A}$



**Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)**



**Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)**

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

## 6. Electrical Characteristics

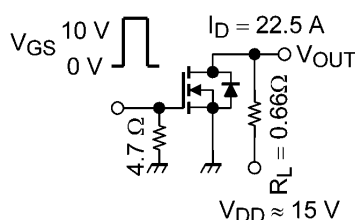
### 6.1. Static Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$	—	—	$\pm 0.1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$	—	—	10	$\mu\text{A}$
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}$ , $V_{GS} = 0\text{ V}$	30	—	—	V
Drain-source breakdown voltage (Note 6)	$V_{(BR)DSX}$	$I_D = 10\text{ mA}$ , $V_{GS} = -20\text{ V}$	15	—	—	V
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}$ , $I_D = 0.5\text{ mA}$	1.3	—	2.3	V
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 4.5\text{ V}$ , $I_D = 22.5\text{ A}$	—	2.8	3.6	$\text{m}\Omega$
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}$ , $I_D = 22.5\text{ A}$	—	1.8	2.2	$\text{m}\Omega$

Note 6: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	—	2230	—	pF
Reverse transfer capacitance	$C_{rss}$		—	160	—	pF
Output capacitance	$C_{oss}$		—	650	—	pF
Switching time (rise time)	$t_r$	See Fig. 6.2.1	—	9	—	ns
Switching time (turn-on time)	$t_{on}$		—	14	—	ns
Switching time (fall time)	$t_f$		—	24	—	ns
Switching time (turn-off time)	$t_{off}$		—	68	—	ns



Duty  $\leq 1\%$ ,  $t_w = 10\text{ }\mu\text{s}$

Fig. 6.2.1 Switching Time Test Circuit

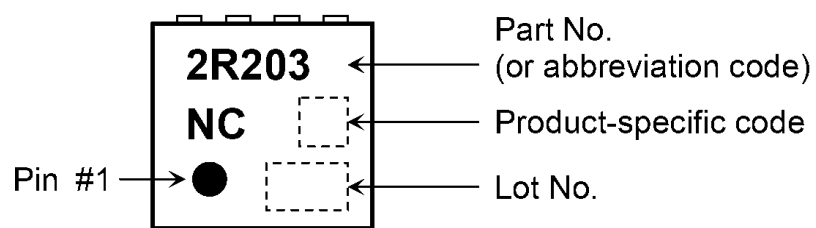
### 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 15\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 45\text{ A}$	—	34	—	nC
Gate-source charge 1	$Q_{gs1}$		—	8	—	nC
Gate-drain charge	$Q_{gd}$		—	6	—	nC

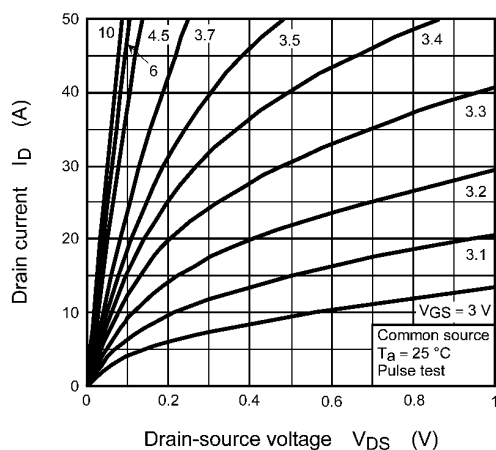
### 6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (1 ms) (Note 7)	$I_{DRP}$	—	—	—	200	A
Diode forward voltage	$V_{DSF}$	$I_{DR} = 45\text{ A}$ , $V_{GS} = 0\text{ V}$	—	—	-1.2	V

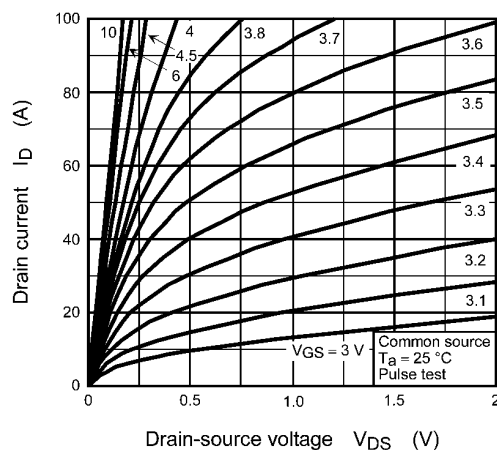
Note 7: Ensure that the channel temperature does not exceed  $150\text{ }^{\circ}\text{C}$ .

**7. Marking****Fig. 7.1 Marking**

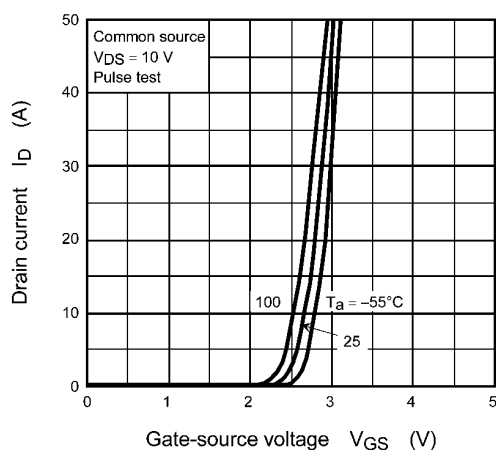
# 8. Characteristics Curves (Note)



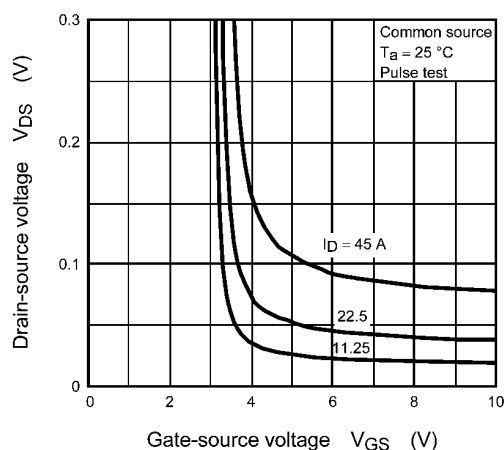
**Fig. 8.1  $I_D - V_{DS}$**



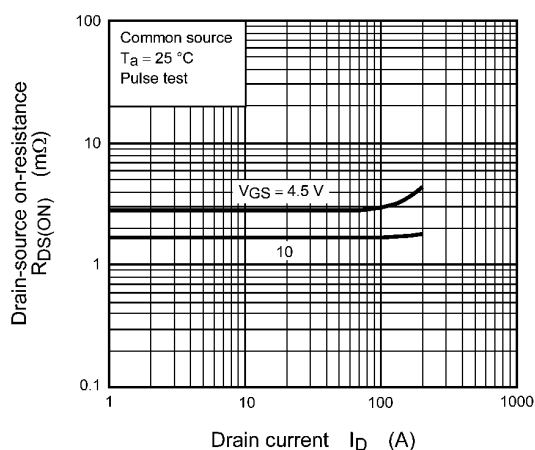
**Fig. 8.2  $I_D - V_{DS}$**



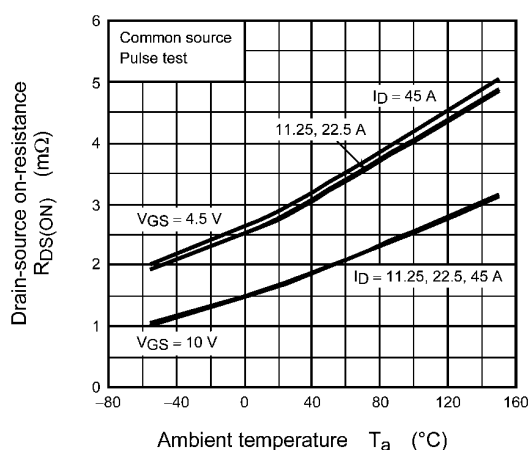
**Fig. 8.3  $I_D - V_{GS}$**



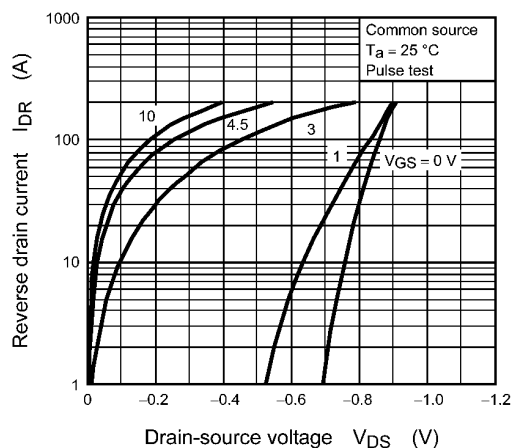
**Fig. 8.4  $V_{DS} - V_{GS}$**



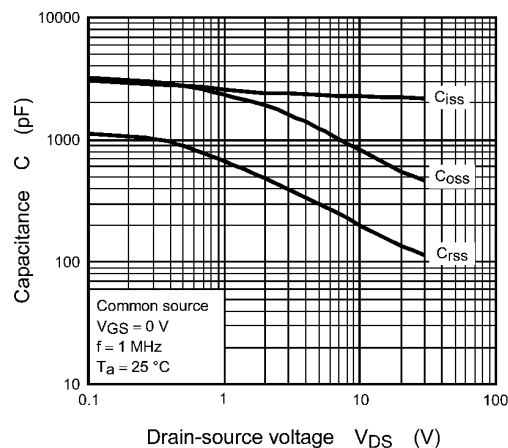
**Fig. 8.5  $R_{DS(ON)} - I_D$**



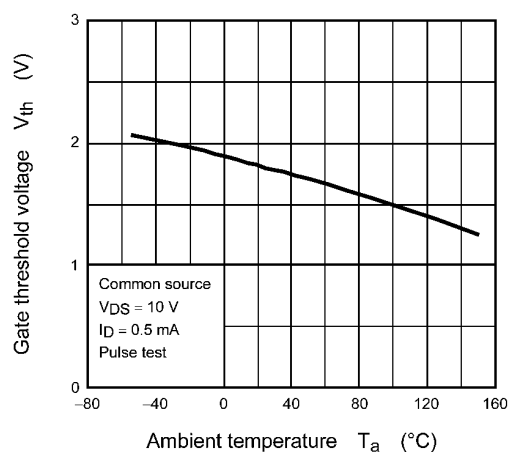
**Fig. 8.6  $R_{DS(ON)} - T_a$**



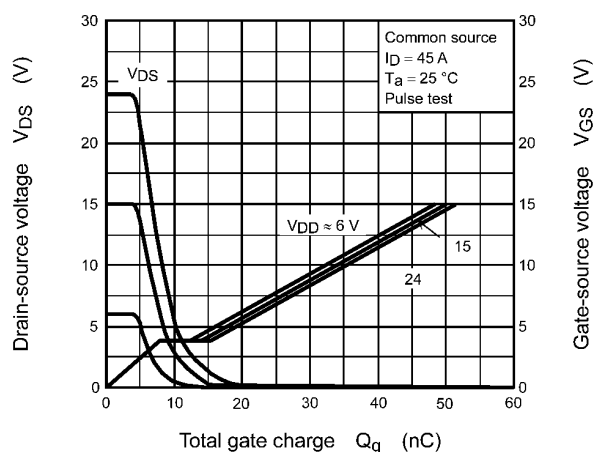
**Fig. 8.7  $I_{DR} - V_{DS}$**



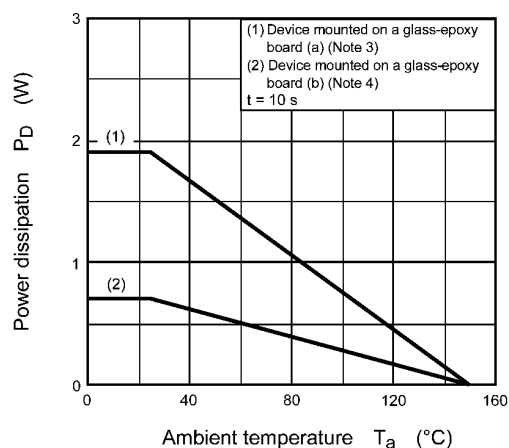
**Fig. 8.8 Capacitance -  $V_{DS}$**



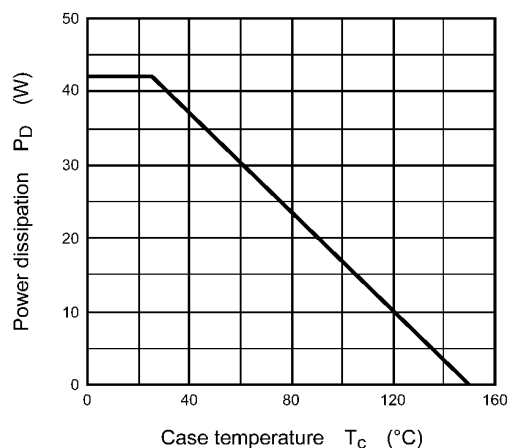
**Fig. 8.9  $V_{th} - T_a$**



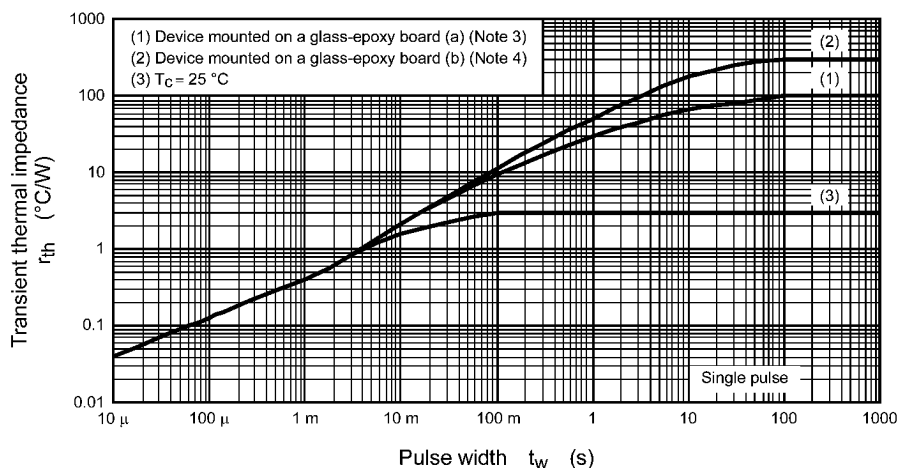
**Fig. 8.10 Dynamic Input/Output Characteristics**



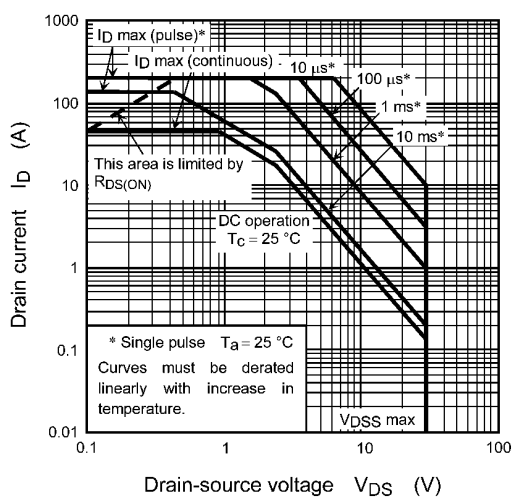
**Fig. 8.11  $P_D - T_a$   
(Guaranteed Maximum)**



**Fig. 8.12  $P_D - T_c$   
(Guaranteed Maximum)**



**Fig. 8.13  $r_{th} - t_w$**   
 (Guaranteed Maximum)

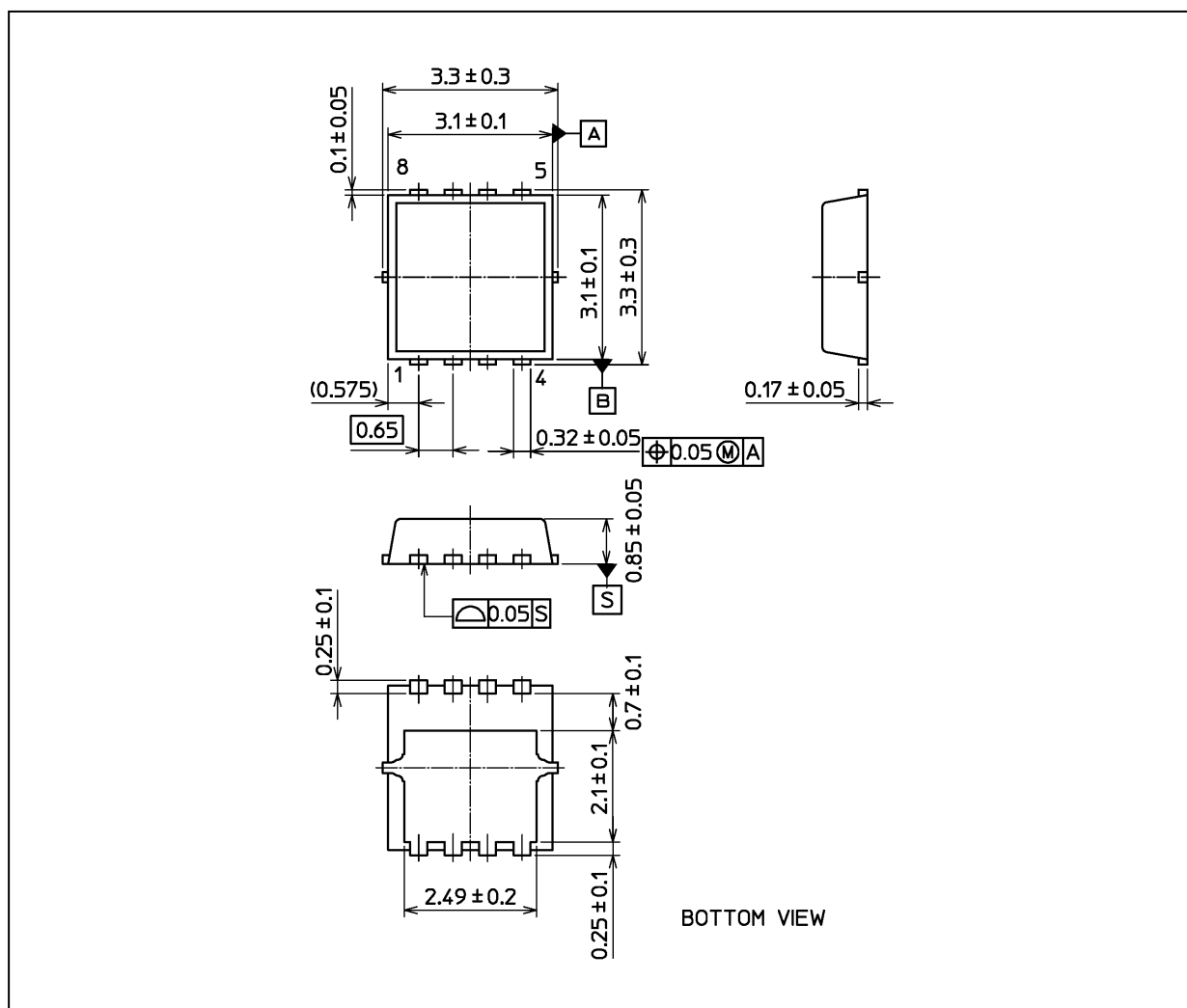


**Fig. 8.14 Safe Operating Area**  
 (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance



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